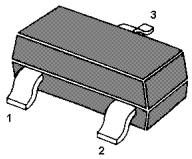
MMBTSC3265

NPN Silicon Epitaxial Planar Transistor

for low frequency power amplifier applications
and power switching application.

The transistor is subdivided into two groups, O and Y according to its DC current gain.



1. Base 2. Emitter 3. Collector

TO-236 Plastic Package

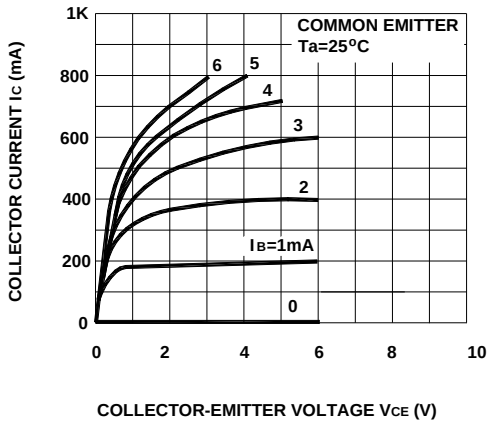
Absolute Maximum Ratings (T_a = 25 °C)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	35	V
Collector Emitter Voltage	V_{CEO}	30	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	800	mA
Base Current	I_B	160	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{Stg}	-55 to +150	°C

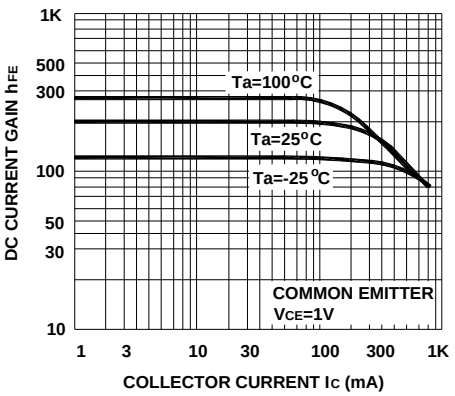
Characteristics at T_{amb}=25 °C

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain					
at V_{CE}=1V, I_C=100mA					
Current Gain Group O	h_{FE}	100	-	200	-
Y	h_{FE}	160	-	320	-
at V_{CE}=1V, I_C=800mA	h_{FE}	40	-	-	-
Collector Cutoff Current					
at V_{CB}=30V	I_{CBO}	-	-	100	nA
Emitter Cutoff Current					
at V_{EB}=5V	I_{EBO}	-	-	100	nA
Collector Emitter Breakdown Voltage					
at I_C=10mA	$V_{(BR)CEO}$	30	-	-	V
Emitter Base Breakdown Voltage					
at I_E=1mA	$V_{(BR)EBO}$	5	-	-	V
Collector Emitter Saturation Voltage					
at I_C=500mA, I_B=20mA	$V_{CE(sat)}$	-	-	0.5	V
Transition Frequency					
at V_{CE}=5V, I_C=10mA, f=100MHz	f_T	-	120	-	MHz
Base Emitter Voltage					
at I_C=10mA, V_{CE}=1V	V_{BE}	0.5	-	0.8	V
Collector Output Capacitance					
at V_{CB}=10V, f=1MHz	C_{OB}	-	13	-	pF

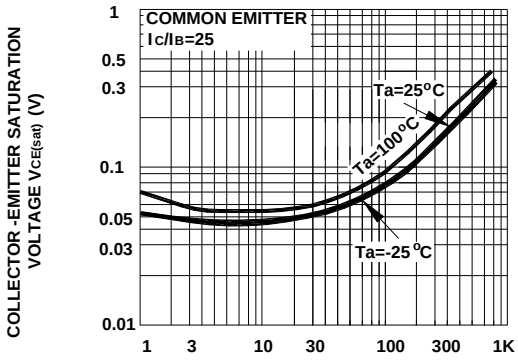
I_C - V_{CE}



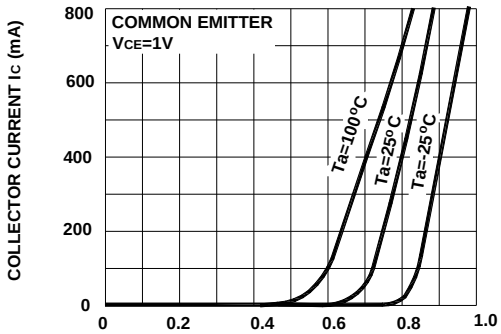
h_{FE} - I_C



$V_{CE(sat)}$ - I_C



I_C - V_{BE}



Pc - Ta